



TO-92L Plastic-Encapsulate Transistors

2SC2236 TRANSISTOR (NPN)

FEATURE

- Complementary to 2SA966 and 3 Watts Output Applications.

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

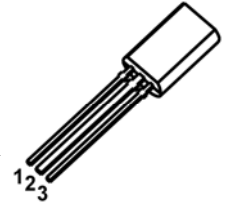
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	1.5	A
P _C	Collector Power Dissipation	0.9	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

TO-92L

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C = 1mA , I _E =0	30			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = 10mA , I _B =0	30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =30V , I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V , I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =2 V, I _C = 500mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 1.5 A, I _B = 0.03A			2	V
Base-emitter voltage	V _{BE}	I _C = 500 mA, V _{CE} = 2V			1	V
Transition frequency	f _T	V _{CE} = 2V, I _C = 500mA		120		MHz
Collector output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz			30	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320